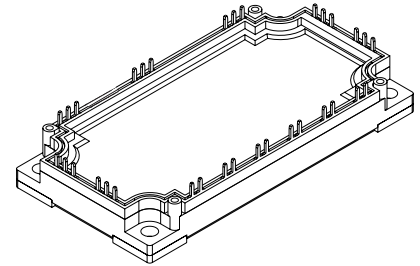
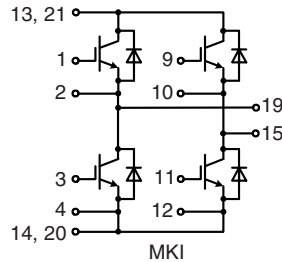


IGBT Modules

H Bridge

Short Circuit SOA Capability
Square RBSOA

$$\begin{aligned} I_{C25} &= 125 \text{ A} \\ V_{CES} &= 1200 \text{ V} \\ V_{CE(sat) \text{ typ.}} &= 3.3 \text{ V} \end{aligned}$$



IGBTs

Symbol	Conditions	Maximum Ratings	
V_{CES}	$T_{VJ} = 25^{\circ}\text{C to } 150^{\circ}\text{C}$	1200	V
V_{GES}		± 20	V
I_{C25}	$T_C = 25^{\circ}\text{C}$	125	A
I_{C80}	$T_C = 80^{\circ}\text{C}$	85	A
I_{CM} V_{CEK}	$V_{GE} = \pm 15 \text{ V}; R_G = 5.6 \Omega; T_{VJ} = 125^{\circ}\text{C}$ RBSOA; clamped inductive load; $L = 100 \mu\text{H}$	200 V_{CES}	A
t_{SC}	$V_{CE} = 900 \text{ V}; V_{GE} = \pm 15 \text{ V}; R_G = 5.6 \Omega; T_{VJ} = 125^{\circ}\text{C}$ SCSOA; non-repetitive	10	μs
P_{tot}	$T_C = 25^{\circ}\text{C}$	640	W

Features

- Fast NPT IGBTs
 - low saturation voltage
 - positive temperature coefficient for easy paralleling
 - fast switching
 - short tail current for optimized performance also in resonant circuits
- HiPerFRED™ diode:
 - fast reverse recovery
 - low operating forward voltage
 - low leakage current
- Industry Standard Package
 - solderable pins for PCB mounting
 - isolated copper base plate

Symbol	Conditions	Characteristic Values ($T_{VJ} = 25^{\circ}\text{C}$, unless otherwise specified)			
		min.	typ.	max.	
$V_{CE(sat)}$	$I_C = 100 \text{ A}; V_{GE} = 15 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		3.3 4.0	3.9 V	
$V_{GE(th)}$	$I_C = 4 \text{ mA}; V_{GE} = V_{CE}$	4.5		6.5 V	
I_{CES}	$V_{CE} = V_{CES}; V_{GE} = 0 \text{ V}; T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 125^{\circ}\text{C}$		4.0	1.3 mA mA	
I_{GES}	$V_{CE} = 0 \text{ V}; V_{GE} = \pm 20 \text{ V}$			600 nA	
$t_{d(on)}$ t_r $t_{d(off)}$ t_f E_{on} E_{off}	Inductive load, $T_{VJ} = 125^{\circ}\text{C}$ $V_{CE} = 600 \text{ V}; I_C = 100 \text{ A}$ $V_{GE} = \pm 15 \text{ V}; R_G = 5.6 \Omega$		130 60 365 30 12.0 5.0	ns ns ns ns mJ mJ	
C_{ies}		$V_{CE} = 25 \text{ V}; V_{GE} = 0 \text{ V}; f = 1 \text{ MHz}$		6.5	nF
Q_{Gon}		$V_{CE} = 600 \text{ V}; V_{GE} = \pm 15 \text{ V}; I_C = 100 \text{ A}$		1.1	μC
R_{thJC}		(per IGBT)			0.19 K/W

IXYS reserves the right to change limits, test conditions and dimensions.

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Diodes

Symbol	Conditions	Maximum Ratings	
I_{F25}	$T_C = 25^\circ\text{C}$	200	A
I_{F80}	$T_C = 80^\circ\text{C}$	130	A

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
V_F	$I_F = 100\text{ A}; V_{GE} = 0\text{ V}; T_{VJ} = 25^\circ\text{C}$ $T_{VJ} = 125^\circ\text{C}$	2.3	1.7	2.6
I_{RM} t_{TR}	$I_F = 120\text{ A}; di_F/dt = -750\text{ A}/\mu\text{s}; T_{VJ} = 125^\circ\text{C}$ $V_R = 600\text{ V}; V_{GE} = 0\text{ V}$	82		A
			200	
R_{thJC}	(per diode)			0.3

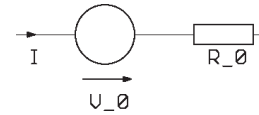
Module

Symbol	Conditions	Maximum Ratings	
T_{VJ}	operating	-40...+125	$^\circ\text{C}$
T_{JM}		+150	$^\circ\text{C}$
T_{stg}		-40...+125	$^\circ\text{C}$
V_{ISOL}	$I_{ISOL} \leq 1\text{ mA}; 50/60\text{ Hz}$	2500	V~
M_d	Mounting torque (M5)	3 - 6	Nm

Symbol	Conditions	Characteristic Values		
		min.	typ.	max.
$R_{pin-chip}$			1.8	m Ω
d_S	Creepage distance on surface	10		mm
d_A	Strike distance in air	10		mm
R_{thCH}	with heatsink compound		0.01	K/W
Weight			300	g

Equivalent Circuits for Simulation

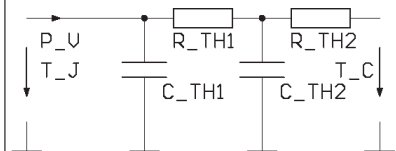
Conduction



IGBT (typ. at $V_{GE} = 15\text{ V}; T_J = 125^\circ\text{C}$)
 $V_o = 2.05\text{ V}; R_o = 19.5\text{ m}\Omega$

Free Wheeling Diode (typ. at $T_J = 125^\circ\text{C}$)
 $V_o = 1.27\text{ V}; R_o = 4.3\text{ m}\Omega$

Thermal Response



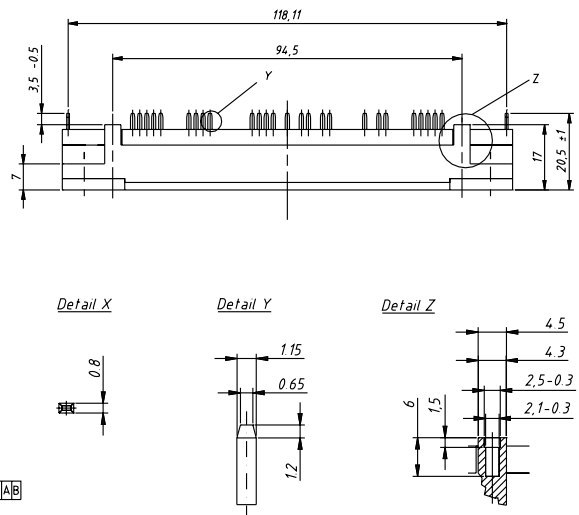
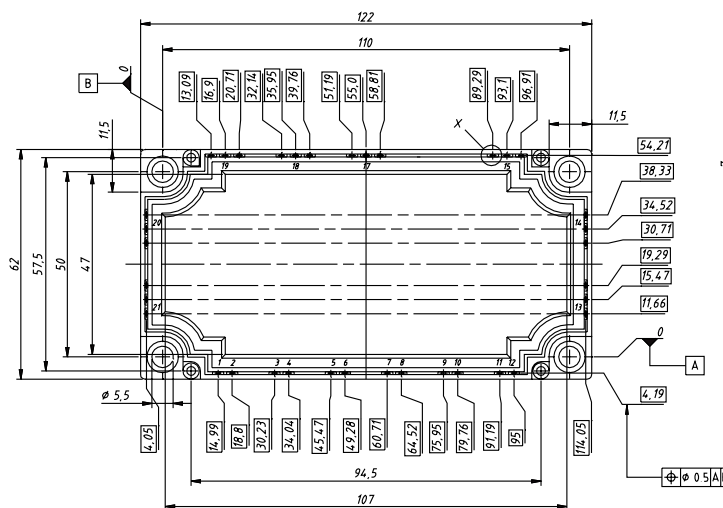
IGBT (typ.)

$C_{th1} = 0.409\text{ J/K}; R_{th1} = 0.14\text{ K/W}$
 $C_{th2} = 2.203\text{ J/K}; R_{th2} = 0.05\text{ K/W}$

Free Wheeling Diode (typ.)

$C_{th1} = 0.301\text{ J/K}; R_{th1} = 0.24\text{ K/W}$
 $C_{th2} = 2.005\text{ J/K}; R_{th2} = 0.062\text{ K/W}$

Dimensions in mm (1 mm = 0.0394")



pins 5, 6, 7, 8 and 17 for MWI only